L Number	Hits	Search Text	DB	Time stamp
1	26	(water with ozone with tank) with (bubbl\$3	JPO;	2004/06/16 15:08
ı	20	sparg\$3 mix\$3) and (ambient "room temperature" temperature)	DERWENT	
2	60	(((water with ozone same(bubbl\$3 sparg\$3	JPO;	2004/06/16 15:06
2	00	mix\$3)) same (wafer semiconductor	DERWENT	2001,00,10 13:00
		substrate))) and (temperature C celsius	DEKWENT	
		ambient)	1	
2	57	((((water with ozone same(bubbl\$3 sparg\$3	JPO;	2004/06/16 15:05
3	5/	mix\$3)) same (wafer semiconductor	DERWENT	2004/00/10 15.05
		substrate))) and (temperature C celsius	DERWENT	
		ambient)) not ((water with ozone with		
		tank) with (bubbl\$3 sparg\$3 mix\$3) and		
		(ambient "room temperature" temperature))		
4	15	(((water with ozone same(bubbl\$3 sparg\$3	JPO;	2004/06/16 15:06
-3	"	mix\$3)) same (wafer semiconductor	DERWENT	
		substrate))) and (temperature "°"	55151.1	
		celsius ambient)		
5	0	6649018.pn. and (deg temperature)	JPO;	2004/06/16 15:09
5	ľ	0043010.pii. una (acg comperature)	DERWENT	2001,00,20 2000
6	1	6649018.pn. and (deg temperature)	USPAT	2004/06/16 15:09
7	3	("5464480" "6080531" "6187216").PN.	USPAT	2004/06/16 15:09
8	3	(("5464480" "6080531" "6187216").PN.)	USPAT	2004/06/16 15:10
9		and (deg temperature)		
_	422	134/159	USPAT	2004/01/30 10:43
_	1	6340643.pn.	USPAT	2003/08/07 12:36
	4	("5405443" "5599394" "6059880"	USPAT	2003/08/07 12:37
	-	"6245148").PN.		
_	2	("5759918" "5695392").pn.	USPAT	2003/08/14 08:26
_	0	"0776730"	EPO	2003/08/14 08:26
_	Ö	0776730.ipc.	EPO	2003/08/14 08:27
_	Ö	776730.ipc.	EPO	2003/08/14 08:27
	Ō	00776730.ipc.	EPO	2003/08/14 08:27
-	l 0	0776730.ipc.	EPO	2003/08/14 08:28
_	1171	Kubo	EPO	2003/08/14 08:28
_	11	Kubo and retaining	EPO	2003/08/14 08:28
_	2	5957764.pn. 5985039.pn. 0793261.ipc.	USPAT; EPO	2003/08/14 11:41
_	3	5957764.pn. 5985039.pn. "0793261"	USPAT; EPO	2003/08/14 11:42
_	1	"0793261"	USPAT; EPO	2003/08/14 11:43
_	0	ep.0793261.	USPAT; EPO	2003/08/14 11:44
_	1	"00793261"	USPAT; EPO	2003/08/14 11:44
_	0	"00793261"	EPO;	2003/08/14 11:45
			DERWENT	
_	236	156/345.11 156/345.23	USPAT	2003/08/14 13:53
-	2807	134/1.3 134/119 134/120 134/136 134/137	USPAT	2003/08/14 13:54
		134/138 134/140 134/157		
	1336	(134/1.3 134/119 134/120 134/136 134/137	USPAT	2003/08/14 13:55
		134/138 134/140 134/157) and (wafer		
		semiconductor substrate)		
_	877	((134/1.3 134/119 134/120 134/136 134/137	USPAT	2003/08/14 13:56
		134/138 134/140 134/157) and (wafer		
		semiconductor substrate)) and (flip\$4		
		turn\$4 rotat\$6)		
-	916	((134/1.3 134/119 134/120 134/136 134/137	USPAT	2003/08/14 13:57
		134/138 134/140 134/157) and (wafer		
		semiconductor substrate)) and etch\$3		
_	423	134/159	USPAT	2004/01/30 10:43
-	162	156/345.11	USPAT;	2004/02/02 14:32
			US-PGPUB	0001155155
-	3	6383724.pn. 5464480.pn. 6187216.pn.	USPAT	2004/02/04 11:02
-	2017	156/345.11 156/345.18 438/689 216/83	USPAT	2004/02/04 11:03
		216/93		
_	50	(156/345.11 156/345.18 438/689 216/83	USPAT	2004/02/04 11:05
		216/93) and (water same ozone)		
-	1	6649018.pn.	EPO;	2004/04/22 10:47
			DERWENT	
_	8	134/113	EPO;	2004/04/22 10:47
			DERWENT	
		134/113	USPAT	2004/04/22 10:48
-	815	1		
-	815 421	water same ozone same (sparger bubbl\$3)	EPO; DERWENT	2004/06/03 15:23

_	1369	water same ozone same (sparger bubbl\$3)	USPAT:	2004/06/03 15:24
		, , , , , , , , , , , , , , , , , , ,	US-PGPUB	2001,00,00 10121
-	647	water with ozone with (sparger bubbl\$3)	USPAT;	2004/06/03 15:25
			US-PGPUB	
-	26	"5750440"	USPAT	2004/06/04 14:25
-	3472	water and ozone and tank	EPO; JPO;	2004/06/16 12:41
	2407		DERWENT	0004/06/16 10 11
_	3407	water and ozone and tank	JPO;	2004/06/16 12:41
_	2825	 water same ozone same tank	DERWENT JPO;	2004/06/16 12:41
-	2023	water same ozone same tank	DERWENT	2004/06/16 12:41
_	2216	water with ozone with tank	JPO:	2004/06/16 12:42
	35.5	wadda waten dadiid waten tanin	DERWENT	2001,00,10 12.12
_	738	(water with ozone with tank) and (bubbl\$3	JPO;	2004/06/16 12:42
1		sparg\$3 mix\$3)	DERWENT	
-	651	water with ozone with tank)same(bubbl\$3	JPO;	2004/06/16 12:52
		sparg\$3 mix\$3	DERWENT	
-	539	water with ozone with tank)with(bubbl\$3	JPO;	2004/06/16 14:57
	22	sparg\$3 mix\$3	DERWENT	0004/06/16 10 45
-	22	<pre>(water with ozone with tank)with(bubbl\$3 sparg\$3 mix\$3) and (wafer semiconductor</pre>	JPO; DERWENT	2004/06/16 12:45
		substrate)	DERWENT	1
	2391	water with ozone same(bubbl\$3 sparg\$3	JPO;	2004/06/16 12:52
	2001	mix\$3)	DERWENT	2004/00/10 12.52
-	99	(water with ozone same(bubbl\$3 sparg\$3	JPO;	2004/06/16 15:04
ĺ		mix\$3)) same (wafer semiconductor	DERWENT	
		substrate)		
-	84	((water with ozone same(bubbl\$3 sparg\$3	JPO;	2004/06/16 13:58
		mix\$3)) same (wafer semiconductor	DERWENT	
		substrate)) not ((water with ozone with		
		tank) with (bubbl\$3 sparg\$3 mix\$3) and		
,		(wafer semiconductor substrate))		